SCT4036KW7HR



Automotive Grade N-channel SiC power MOSFET

Datasheet

V _{DSS}	1200V
R _{DS(on)} (Typ.)	36mΩ
I _D ^{*1}	40A
P_D	150W

Outline TO-263-7L (Tab) (1)(2)(3)(4)(5)(6)(7)

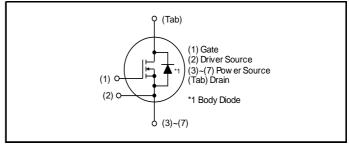
Features

- 1) Qualified to AEC-Q101
- 2) Low on-resistance
- 3) Fast switching speed
- 4) Fast reverse recovery
- 5) Easy to parallel
- 6) Simple to drive
- 7) Pb-free lead plating; RoHS compliant

Application

- Automobile
- Switch mode power supplies

•Inner circuit



Please note Driver Source and Power Source are not exchangeable. Their exchange might lead to malfunction.

Packaging specifications

	Packing	Embossed tape
	Reel size (mm)	330
Type	Tape width (mm)	24
Type	Basic ordering unit (pcs)	1000
	Taping code	TL
	Marking	SCT4036KW

●Absolute maximum ratings (T_c = 25°C)

Parameter		Symbol	Value	Unit
Drain - source voltage		V_{DSS}	1200	V
Continuous drain and source current	\/ _\/	, , *1	40	А
$T_c = 100$ °C	$V_{GS} = V_{GS_on}$	I _D , I _S *1	28	Α
Pulsed drain current	$V_{GS} = V_{GS_on}$	l _{D,pulse} *2	84	Α
Body diode pulsed forward current	$V_{GS} = 0 V$	I _{S,pulse} *3	40	А
Body diode surge forward current	$V_{GS} = 0 V$	I _{S,pulse} *4	84	Α
Gate - source voltage (DC)		V_{GSS_DC}	-4 to +21	V
Gate - source surge voltage (t _{surge} < 300ns)		$V_{\rm GSS_surge}^{*5}$	-4 to +23	V
Recommended turn-on gate - source drive voltage		${\sf V_{GS_on}}^{*6}$	+15 to +18	V
Recommended turn-off gate - source drive voltage		V_{GS_off}	0	V
Virtual junction temperature		T_{vj}	175	°C
Range of storage temperature		T_{stg}	-40 to +175	°C

ullet Electrical characteristics (T_{vj} = 25°C unless otherwise specified)

Parameter	Symbol	Conditions		Values		
raiailletei	Symbol	Conditions	Min.	Тур.	Max.	Unit
Drain - Source breakdown voltage	W	$V_{GS} = 0 \text{ V}, I_D = 9.2 \text{mA}$				V
	$V_{(BR)DSS}$	$T_{vj} = 25^{\circ}C$	1200	-	-	V
		$V_{GS} = 0 \text{ V}, V_{DS} = 1200 \text{V}$				
Zero Gate voltage Drain current	I _{DSS}	$T_{vj} = 25^{\circ}C$	-	1	80	μA
Diam current		T _{vj} = 150°C	-	10	-	
Gate - Source leakage current	I _{GSS+}	$V_{GS} = +21V$, $V_{DS} = 0V$	-	-	100	nA
Gate - Source leakage current		$V_{GS} = -4V$, $V_{DS} = 0V$	ı	ı	-100	nA
Gate threshold voltage	$V_{GS(th)}^{*7}$	$V_{DS} = 10V, I_D = 11.1mA$	2.8	ı	4.8	V
		$V_{GS} = 18V, I_{D} = 21A$				
Static Drain - Source on - state resistance	R _{DS(on)} *8	$T_{vj} = 25^{\circ}C$	-	36	47	mΩ
on state registration		T _{vj} = 150°C	-	72	-	
Gate input resistance	R_{G}	f = 1MHz, open drain	-	1	-	Ω

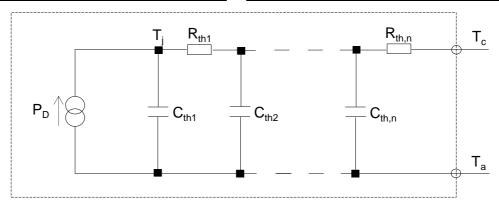
●Thermal resistance

Parameter	Symbol	Values			Linit
		Min.	Тур.	Max.	Unit
Thermal resistance, junction - case	R _{thJC} *9	-	0.79	1.0	K/W

● Typical Transient Thermal Characteristics

Symbol	Value	Unit
R _{th1}	1.2 ×10 ⁻¹	
R _{th2}	3.2 ×10 ⁻¹	K/W
R_{th3}	3.6 ×10 ⁻¹	

Symbol	Value	Unit
C _{th1}	5.8 × 10 ⁻⁴	
C _{th2}	2.7 ×10 ⁻³	Ws/K
C _{th3}	2.7 ×10 ⁻²	



Electrical characteristics ($T_{vj} = 25$ °C unless otherwise specified)

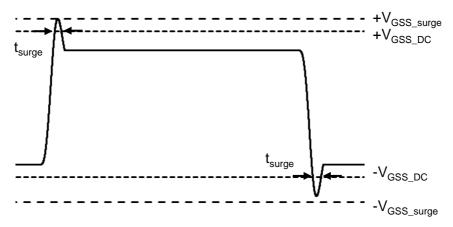
Doromotor	Symbol Conditions -		Values			
Parameter		Conditions	Min.	Тур.	Max.	Unit
Transconductance	g _{fs} *8	$V_{DS} = 10V, I_{D} = 21A$	-	11	-	S
Input capacitance	C _{iss}	V _{GS} = 0V	-	2335	-	
Output capacitance	C _{oss}	V _{DS} = 800V	1	70	ı	pF
Reverse transfer capacitance	C_{rss}	f = 1MHz	-	5	1	
Effective output capacitance, energy related	C _{o(er)}	$V_{GS} = 0V$ $V_{DS} = 0V \text{ to } 800V$	1	84	-	pF
Total Gate charge	Q _g *8	$V_{DS} = 800V$ $I_{D} = 21A$	ı	91	-	
Gate - Source charge	Q _{gs} *8	$V_{GS} = 18V$	-	20	-	nC
Gate - Drain charge	Q _{gd} *8	See Fig. 1-1, 1-2.	-	24	-	
Turn - on delay time	t _{d(on)} *8	$V_{DS} = 800V$	ı	8.1	-	
Rise time	t _r *8	$I_D = 21A$ $V_{GS} = +18V / 0V$	-	15	-	20
Turn - off delay time	t _{d(off)} *8	$R_G = 3.3\Omega$, L = 250µH E_{on} includes diode	-	29	-	ns
Fall time	t _f *8	reverse recovery $L_{\sigma} = 50 \text{nH}, C_{\sigma} = 10 \text{pF}$	-	9.6	-	
Turn - on switching loss	E _{on} *8	See Fig. 2-1, 2-2, 2-3.	-	239	-	1
Turn - off switching loss	E _{off} *8		-	26	-	μJ

●Body diode electrical characteristics (Source-Drain) (T_{vj} = 25°C unless otherwise specified)

Parameter	Symbol	Conditions		Values		Unit
- Farameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Forward voltage	V _{SD} *8	$V_{GS} = 0V, I_{D} = 21A$	ı	3.3	ı	V
Reverse recovery time	t _{rr} *8	$I_F = 21A$ $V_R = 800V$	ı	9.2	ı	ns
Reverse recovery charge	Q _{rr} *8	di/dt = 3700A/µs	ı	140	ı	nC
Peak reverse recovery current	I _{rrm} *8	$L_{\sigma} = 50$ nH, $C_{\sigma} = 10$ pF See Fig. 3-1, 3-2.	-	31	-	А

^{*1} Limited by maximum T_{vj} and for Max. R_{thJC}.

*5 Example of acceptable V_{GS} waveform



Please note especially when using driver source that V_{GSS_surge} must be in the range of absolute maximum rating.

- *6 Please be advised not to use SiC-MOSFETs with V_{GS} below 10V as doing so may cause thermal runaway.
- *7 Tested after applying $V_{GS} = 21V$ for 100ms.
- *8 Pulsed
- *9 Measured conformable to JESD51-14.

See the application note "rthjc_measurement_and_usage_an-e.pdf". Link

URL: https://fscdn.rohm.com/en/products/databook/applinote/discrete/common/rthjc_measurement_and_usage_an-e.pdf

^{*2} PW \leq 10µs, Duty cycle \leq 1%

^{*3} Only for body-diode, Repititive pulse, PW ≤ 500ns, Duty cycle ≤ 5%

^{*4} When used as a protective function, PW ≤ 10µs

Fig.1 Power Dissipation Derating Curve

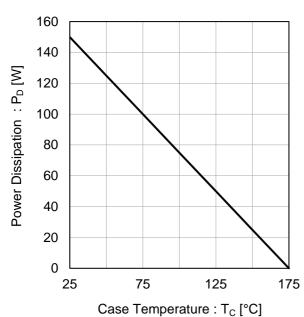


Fig.2 Maximum Safe Operating Area

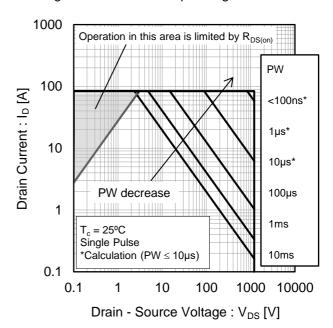
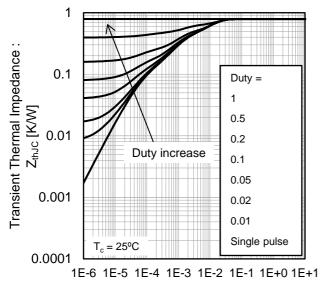
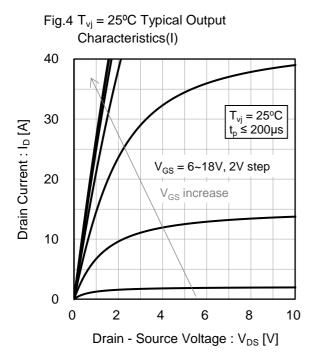


Fig.3 Typical Transient Thermal Impedance vs. Pulse Width



Pulse Width: PW [s]



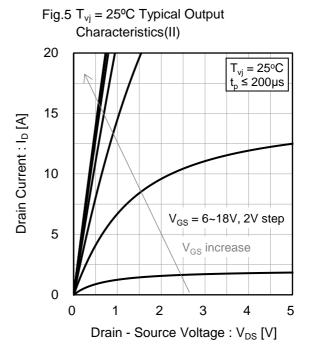
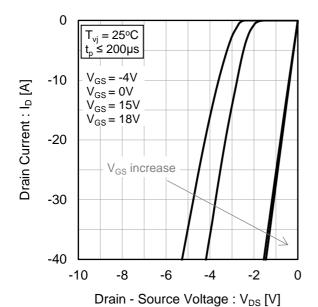


Fig.6 T_{vj} = 25°C 3rd Quadrant Characteristics



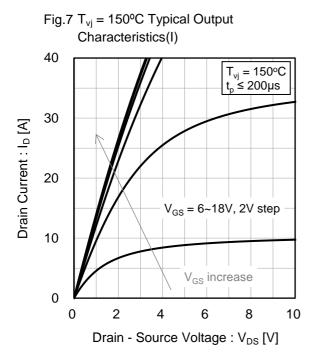


Fig.8 T_{vj} = 150°C Typical Output Characteristics(II) 20 $T_{vj} = 150^{\circ}C$ $t_p \le 200\mu s$ 15 Drain Current : I_D [A] 10 5 V_{GS} = 6~18V, 2V step V_{GS} increase 0 0 1 3 5 Drain - Source Voltage : V_{DS} [V]

Fig.9 $T_{vj} = 150^{\circ}$ C 3rd Quadrant Characteristics $T_{vj} = 150^{\circ}C$ ≤ 200µs $V_{GS} = -4V$ -10 Drain Current: I_D [A] $V_{GS} = 0V$ $V_{GS} = 15V$ $V_{GS} = 18V$ -20 V_{GS} increase -30 -40 -8 -6 -2 0 -10 -4 Drain - Source Voltage: V_{DS} [V]

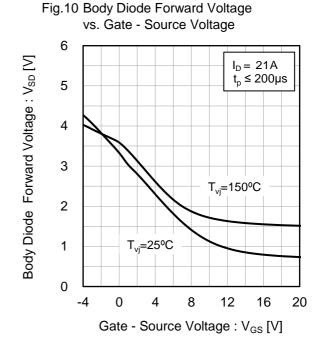


Fig.11 Typical Transfer Characteristics (I)

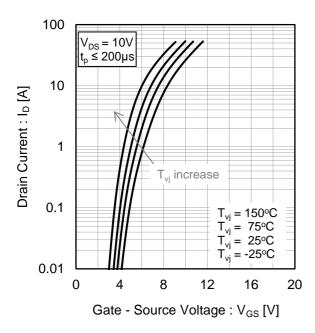


Fig.12 Typical Transfer Characteristics (II)

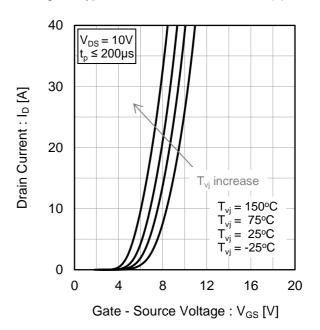


Fig.13 Gate Threshold Voltage vs. Virtual Junction Temperature

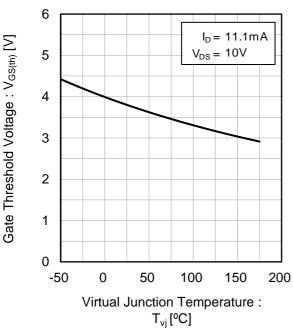
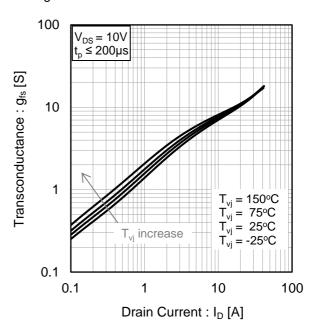
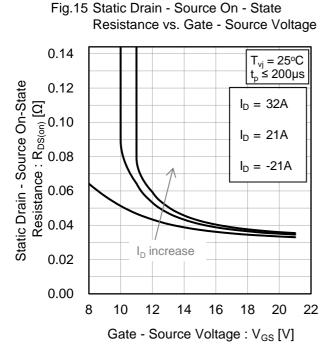


Fig.14 Transconductance vs. Drain Current





Resistance vs. Virtual Junction Temperature 0.14 $V_{GS} = 18V$ $t_p \le 200 \mu s$ Static Drain - Source On-State 0.12 Resistance : R_{DS(on)} [Ω] 80.0 80.0 80.0 40.0 $I_{D} = 32A$ $I_{D} = 21A$ $I_D = -21A$ I_D increase 0.02 0.00 0 -50 50 100 150 200 Virtual Junction Temperature: T_{vi} [°C]

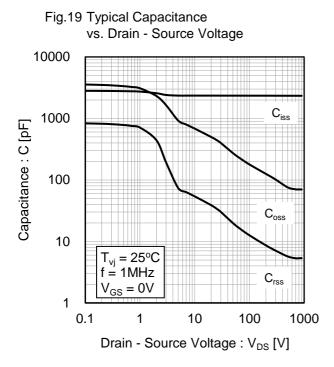
Fig.16 Static Drain - Source On - State

Fig.17 Static Drain - Source On - State Resistance vs. Drain Current T_{vi} = 150°C $T_{vj} = 125^{\circ}C$ Static Drain - Source On-State = 75°C $T_{vj} = 25^{\circ}C$ Resistance : $R_{DS(on)}\left[\Omega\right]$ $T_{vj}^{vj} = -25^{\circ}C$ 0.1 T_{vj} increase 0.01 $V_{GS} = 18V$ ≤ 200µs 0.001 10 100 Drain Current: ID [A]

Voltage vs. Virtual Junction Temperature 1.1 Normalized Drain - Source Breakdown Voltage 1.0 $V_{GS} = 0 V$ $I_D = 9.2 \text{ mA}$ 0.9 0 -50 50 100 200 150 Virtual Junction Temperature: T_{vi} [°C]

Fig.18 Normalized Drain - Source Breakdown

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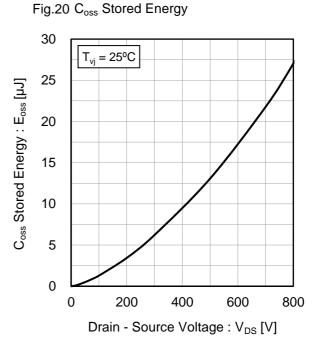


Fig.21 Dynamic Input Characteristics

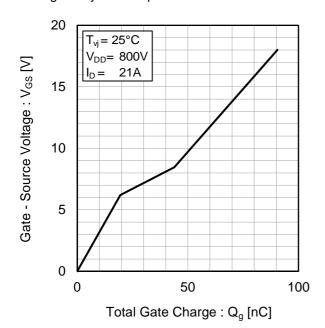


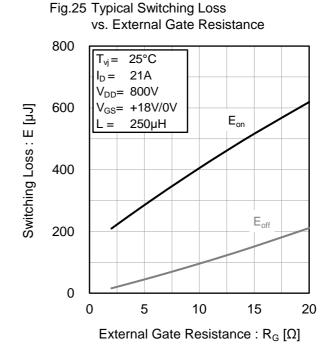
Fig.22 Typical Switching Time

vs. External Gate Resistance 120 25°C 21A $I_D =$ 100 $V_{DD} = 800V$ V_{GS}= +18V/0V Switching Time: t [ns] 250µH 80 60 $t_{d(on)}$ 40 20 t_f 0 0 5 10 15 20 External Gate Resistance : $R_G[\Omega]$

vs. Drain - Source Voltage 800 25°C 21A $I_D =$ $V_{GS} = +18V/0V$ 600 $R_G = 3.3\Omega$ Switching Loss: E [µJ] 250µH L= 400 E_{on} 200 E_{off} 0 200 400 600 800 Drain - Source Voltage: V_{DS} [V]

Fig.23 Typical Switching Loss

Fig.24 Typical Switching Loss vs. Drain Current 800 25°C $V_{DD} = 800V$ +18V/0V $V_{GS} =$ 600 Switching Loss: E [µJ] $R_G =$ 3.3Ω 250µH 400 E_{on} 200 $\mathsf{E}_{\mathsf{off}}$ 0 0 10 20 30 40 Drain Current: I_D [A]



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Measurement circuits and waveforms

Fig.1-1 Gate Charge Measurement Circuit

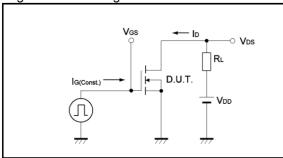


Fig.2-1 Switching Characteristics Measurement Circuit

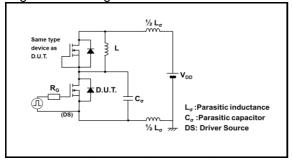


Fig.2-3 Waveforms for Switching Energy Loss

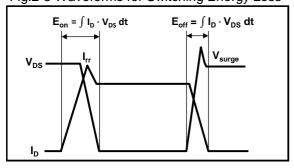


Fig.3-1 Reverse Recovery Time Measurement Circuit

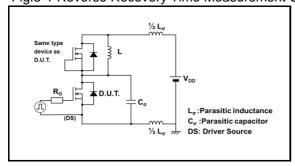


Fig.1-2 Gate Charge Waveform

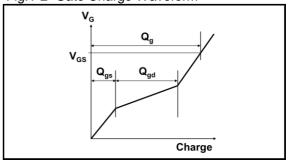


Fig.2-2 Waveforms for Switching Time

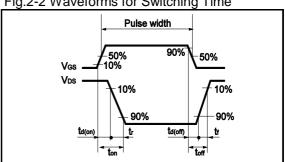
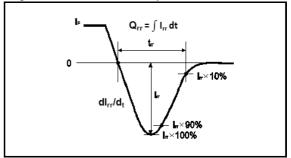
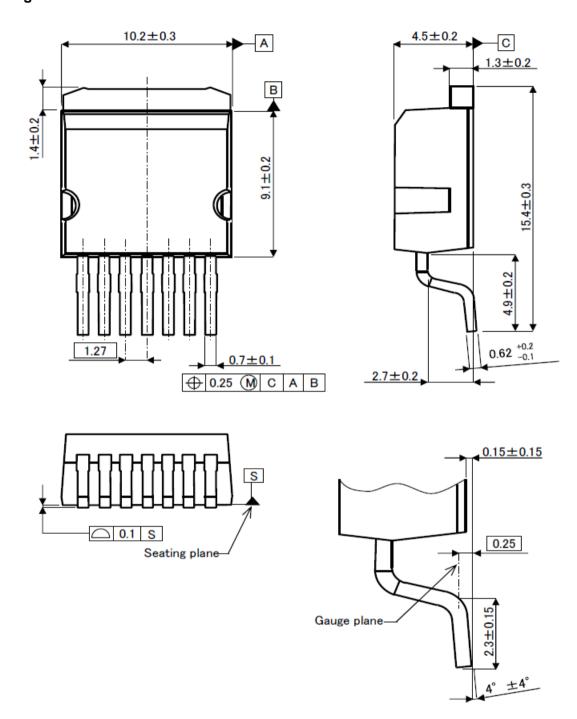


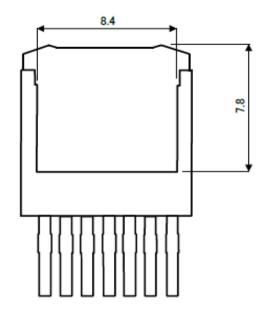
Fig.3-2 Reverse Recovery Waveform



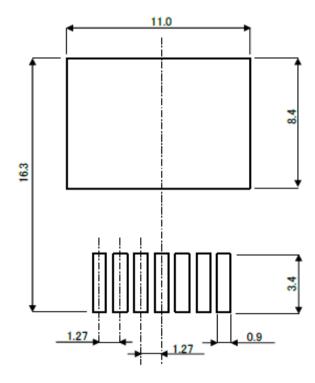
Package Dimensions



Unit: mm

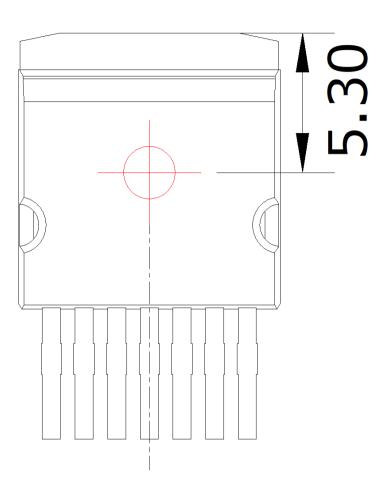


RECOMMENDED FOOTPRINT DIMENSIONS



Unit: mm

●Die Bonding Layout





- •Front view of the packaging.
- •Dimensions are design values.
- •If the heat sink is to be installed, it should be in contact with the die bonding point.

Unit: mm

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